

NVHL020N090SC1

Silicon Carbide MOSFET, N-Channel, 900 V, 20 mΩ, TO247-3L

Product Overview

For complete documentation, see the data sheet.

Silicon Carbide (SiC) MOSFET uses a completely new technology that provide superior switching performance and higher reliability compared to Silicon. In addition, the low ON resistance and compact chip size ensure low capacitance and gate charge. Consequently, system benefits include highest efficiency, faster operation frequency, increased power density, reduced EMI, and reduced system size.

Features

- Qualified for Automotive According to AEC-Q101
- 900V rated
- Max RDS(on) = 28 mΩ at Vgs = 15V, Id = 60A
- High Speed Switching and Low Capacitance
- 100% UIL Tested
- Devices are RoHS Compliant

Applications

- Automotive PFC
- Automotive DC/DC

Benefits

- Automotive Grade

End Products

- Automotive DC/DC converter for EV/PHEV
- Automotive On Board Charger

Part Electrical Specifications											
Product	Pricing (\$/Unit)	Compliance	Status	Family	Blocking Voltage BV _{DSS} (V)	I _{D(max)} (A)	R _{DS(on)} Typ @ 25°C (mΩ)	Q _g Total (nC)	Output Capacitance (pF)	T _j Max (°C)	Package Type
NVHL020N090SC1	16.4195		Active	M2	900	118	20	196	296	175	TO-247-3LD